



ELECTRONICS, INC.
 44 FARRAND STREET
 BLOOMFIELD, NJ 07003
 (973) 748-5089
<http://www.nteinc.com>



NTE2672 Silicon NPN Transistor High Gain, Low Frequency, General Purpose Amp TO92 Type Package

Features:

- High DC Current Gain: $h_{FE} = 800$ to 3200
- Low Collector–Emitter Saturation Voltage: $V_{CE(sat)} = 0.5V$ Max
- High Collector–Base Voltage: $V_{EBO} \geq 15V$

Applications:

- Low Frequency, General Purpose Amp
- Various Drivers
- Muting Circuit

Absolute Maximum Ratings: ($T_A = +25^\circ C$ unless otherwise specified)

Collector–Base Voltage, V_{CBO}	60V
Collector–Emitter Voltage, V_{CEO}	50V
Emitter–Base Voltage, V_{EBO}	15V
Collector Current, I_C	
Continuous	200mA
Pulsed	300mA
Base Current, I_B	40mA
Collector Dissipation, P_C	600mW
Operating Junction Temperature, T_J	+150°C
Storage Temperature Range, T_{stg}	-55° to +150°C

Electrical Characteristics: ($T_A = +25^\circ C$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB} = 40V, I_E = 0$	-	-	0.1	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB} = 10V, I_C = 0$	-	-	0.1	μA
DC Current Gain	h_{FE}	$V_{CE} = 5V, I_C = 10mA$	800	1500	3200	
		$V_{CE} = 5V, I_C = 100mA$	600	-	-	
Gain–Bandwidth Product	f_T	$V_{CE} = 10V, I_C = 10mA$	-	250	-	MHz
Common Base Output Capacitance	c_{ob}	$V_{CB} = 10V, f = 1MHz$	-	4.0	-	pF
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 100mA, I_B = 2mA$	-	0.12	0.5	V
Base–Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 100mA, I_B = 2mA$	-	0.85	1.2	V
Collector–Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 10\mu A, I_E = 0$	60	-	-	V
Collector–Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1mA, I_B = 0$	50	-	-	V
Emitter–Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 10\mu A, I_C = 0$	15	-	-	V

